Sem-III (Comp) Electronic Circuits & Comm. Fundamentals (CBGS & Revised)

QP Code: 30607

Time:-3 Hrs

Marks: 80

| N.B. | : 1. Question ONE is compulsory | |
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| | 2. Solve any THREE out of remaining questions | |
| - 12 | 3 Draw neat and along discovery | |
| | 4. Assume suitable data if required. | QF |
| | | - PS |
| Q. 1. | A. Justify that JFET can be used as a Voltage Variable Resistor | 5 |
| | B. With neat diagram explain any one application of Zero-Crossing Detector | 5 |
| | C. With neat block diagram explain how PLL can be used to generate large number of | frequencies |
| | from a single reference frequency. | 5 |
| | D. Explain with suitable example what do you understand by signal multiplexing? | 5 |
| Q. 2 | A. Derive an expression for trans-conductance for JFET. | 10 |
| | B. List down various parameters of Opamp along with their typical values for IC741. A | lso explain |
| | what the significance of CMRR and Slew Rate is? | 10 |
| Q. 3 | A. Explain how operational amplifier can be used for taking average of three signals. | 5 |
| | B. Explain fly wheel effect in Class C amplifier. | 5 |
| | C. Explain Nyquist criteria. | 5 |
| | D. Determine the magnitude of g_m for a IFET with $I_{DSS} = 8$ mA and $V_P = -4$ V at dc bia. | s points |
| | V_{GS} = -0.5 V and also at V_{GS} = -2.5 V | 5 |
| Q. 4 | A. Explain generation of SSB using phase shift method. | 10 |
| | B. Explain the use of PLL as FM detector. | 10 |
| Q. 5 | A. Explain super heterodyne receiver in detail along with the waveforms at each stage. | 10 |
| | B. Explain the concept of amplitude modulation. | 10 |
| Q.6. | A. Write short note on generation of FM by Armstrong method. | 5 |
| | B. Mention important specifications of ADC and DAC required for communication. | 5 |
| | C. Explain the necessity and significance of modulation in communication. | 5 |
| | D. Compare n-channel and p-channel JFET with respect to their device features and volt | age- |
| | current characteristics. | 5 |
| / | / V | |